

L Number	Hits	Search Text	DB	Time stamp
-	400502	plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/22 12:15
-	803924	oxygen or "o.sub.2" or "o.sub2." or "o2"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/22 12:17
-	1104427	hydrogen or "h.sub.2" or "h.sub2." or "h2"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/22 12:18
-	796149	nitrogen or "n.sub.2" or "n.sub2." or "n2"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/22 12:18
-	1875166	(oxygen or "o.sub.2" or "o.sub2." or "o2") or (hydrogen or "h.sub.2" or "h.sub2." or "h2") or (nitrogen or "n.sub.2" or "n.sub2." or "n2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/22 12:19
-	3645038	treat\$5 or anneal\$5 or expos\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/22 12:21
-	31912	plasma same (treat\$5 or anneal\$5 or expos\$5) same ((oxygen or "o.sub.2" or "o.sub2." or "o2") or (hydrogen or "h.sub.2" or "h.sub2." or "h2") or (nitrogen or "n.sub.2" or "n.sub2." or "n2"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/22 12:21
-	880783	gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/22 14:54
-	33767	ldd or light\$3 adj3 dop\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/22 12:23
-	2422	(plasma same (treat\$5 or anneal\$5 or expos\$5) same ((oxygen or "o.sub.2" or "o.sub2." or "o2") or (hydrogen or "h.sub.2" or "h.sub2." or "h2") or (nitrogen or "n.sub.2" or "n.sub2." or "n2"))) and gate and (ldd or light\$3 adj3 dop\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/22 12:29
-	44119	plasma near5 ((oxygen or "o.sub.2" or "o.sub2." or "o2") or (hydrogen or "h.sub.2" or "h.sub2." or "h2") or (nitrogen or "n.sub.2" or "n.sub2." or "n2"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/22 16:00
-	71247	plasma near10 (treat\$5 or anneal\$5 or expos\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/22 12:30
-	14574	(plasma near5 ((oxygen or "o.sub.2" or "o.sub2." or "o2") or (hydrogen or "h.sub.2" or "h.sub2." or "h2") or (nitrogen or "n.sub.2" or "n.sub2." or "n2"))) same (plasma near10 (treat\$5 or anneal\$5 or expos\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/22 12:30

-	841	((plasma near5 ((oxygen or "o.sub.2" or "o.sub.2." or "o2") or (hydrogen or "h.sub.2" or "h.sub.2." or "h2") or (nitrogen or "n.sub.2" or "n.sub.2." or "n2")))) same (plasma near10 (treat\$5 or anneal\$5 or expos\$5))) and gate and (ldd or light\$3 adj3 dop\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/22 12:31
-	555217	mosfet or mos or fet or misfet or igfet or field adj5 transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/22 12:33
-	2802509	drain or source	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/22 12:34
-	839	((((plasma near5 ((oxygen or "o.sub.2" or "o.sub.2." or "o2") or (hydrogen or "h.sub.2" or "h.sub.2." or "h2") or (nitrogen or "n.sub.2" or "n.sub.2." or "n2")))) same (plasma near10 (treat\$5 or anneal\$5 or expos\$5))) and gate and (ldd or light\$3 adj3 dop\$3)) and ((mosfet or mos or fet or misfet or igfet or field adj5 transistor) or (drain or source))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/22 12:35
-	280306	implant\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/22 12:37
-	656	(((((plasma near5 ((oxygen or "o.sub.2" or "o.sub.2." or "o2") or (hydrogen or "h.sub.2" or "h.sub.2." or "h2") or (nitrogen or "n.sub.2" or "n.sub.2." or "n2")))) same (plasma near10 (treat\$5 or anneal\$5 or expos\$5))) and gate and (ldd or light\$3 adj3 dop\$3)) and ((mosfet or mos or fet or misfet or igfet or field adj5 transistor) or (drain or source))) and implant\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/22 12:37
-	213935	pocket	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/22 12:37
-	53	(((((plasma near5 ((oxygen or "o.sub.2" or "o.sub.2." or "o2") or (hydrogen or "h.sub.2" or "h.sub.2." or "h2") or (nitrogen or "n.sub.2" or "n.sub.2." or "n2")))) same (plasma near10 (treat\$5 or anneal\$5 or expos\$5))) and gate and (ldd or light\$3 adj3 dop\$3)) and ((mosfet or mos or fet or misfet or igfet or field adj5 transistor) or (drain or source))) and implant\$6) and pocket	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/22 13:01
-	624666	(mosfet or mos or fet or misfet or igfet or field adj5 transistor) or pmos or nmos or cmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/22 16:08
-	2544	(etch\$4 or pattern\$4) near30 gate near30 damag\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/22 13:04

-	253	((etch\$4 or pattern\$4) near30 gate near30 damag\$4) and (plasma same (treat\$5 or anneal\$5 or expos\$5) same ((oxygen or "o.sub.2" or "o.sub2." or "o2") or (hydrogen or "h.sub.2" or "h.sub2." or "h2") or (nitrogen or "n.sub.2" or "n.sub2." or "n2"))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/22 14:52
-	63650	passivat\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/22 14:52
-	945231	gate or polysilicon or polysi or (poly or polycrystal\$4) adj2 (si or silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/22 14:56
-	310	passivat\$5 same (gate or polysilicon or polysi or (poly or polycrystal\$4) adj2 (si or silicon)) same (plasma near5 ((oxygen or "o.sub.2" or "o.sub2." or "o2") or (hydrogen of "h.sub.2" or "h.sub2." or "h2") or (nitrogen or "n.sub.2" or "n.sub2." or "n2"))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/22 14:58
-	191	(passivat\$5 same (gate or polysilicon or polysi or (poly or polycrystal\$4) adj2 (si or silicon)) same (plasma near5 ((oxygen or "o.sub.2" or "o.sub2." or "o2") or (hydrogen or "h.sub.2" or "h.sub2." or "h2") or (nitrogen or "n.sub.2" or "n.sub2." or "n2")))) and ((mosfet or mos or fet or misfet or igfet or field adj5 transistor) or pmos or nmos or cmos)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/22 15:55
-	4563	438/585.ccls. or 438/595.ccls. or 438/798 or 438/303.ccls. or 438/305.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/22 16:00
-	554	(438/585.ccls. or 438/595.ccls. or 438/798 or 438/303.ccls. or 438/305.ccls.) and (plasma near5 ((oxygen or "o.sub.2" or "o.sub2." or "o2") or (hydrogen or "h.sub.2" or "h.sub2." or "h2") or (nitrogen or "n.sub.2" or "n.sub2." or "n2"))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/22 16:02
-	459	((438/585.ccls. or 438/595.ccls. or 438/798 or 438/303.ccls. or 438/305.ccls.) and (plasma near5 ((oxygen or "o.sub.2" or "o.sub2." or "o2") or (hydrogen or "h.sub.2" or "h.sub2." or "h2") or (nitrogen or "n.sub.2" or "n.sub2." or "n2")))) and (gate or polysilicon or polysi or (poly or polycrystal\$4) adj2 (si or silicon)) and (drain or source)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/22 16:03
-	390	((438/585.ccls. or 438/595.ccls. or 438/798 or 438/303.ccls. or 438/305.ccls.) and (plasma near5 ((oxygen or "o.sub.2" or "o.sub2." or "o2") or (hydrogen or "h.sub.2" or "h.sub2." or "h2") or (nitrogen or "n.sub.2" or "n.sub2." or "n2")))) and ((mosfet or mos or fet or misfet or igfet or field adj5 transistor) or pmos or nmos or cmos)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/22 16:09

-	369	(((438/585.ccls. or 438/595.ccls. or 438/798 or 438/303.ccls. or 438/305.ccls.) and (plasma near5 ((oxygen or "o.sub.2" or "o.sub.2." or "o2") or (hydrogen or "h.sub.2" or "h.sub2." or "h2") or (nitrogen or "n.sub.2" or "n.sub2." or "n2")))) and ((mosfet or mos or fet or misfet or igfet or field adj5 transistor) or pmos or nmos or cmos)) and (drain or source)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/22 16:11
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L Number	Hits	Search Text	DB	Time stamp
-	11144	ldd	USPAT; US-PGPUB	2004/08/25 10:02
-	139757	pocket	USPAT; US-PGPUB	2004/08/23 11:29
-	10956	punchthrough or punch adj2 through	USPAT; US-PGPUB	2004/08/23 11:29
-	262	pocket with (punchthrough or punch adj2 through)	USPAT; US-PGPUB	2004/08/23 11:29
-	150	ldd and (pocket with (punchthrough or punch adj2 through))	USPAT; US-PGPUB	2004/08/23 15:52
-	122736	anneal\$4	USPAT; US-PGPUB	2004/08/23 15:52
-	150	ldd and (pocket with (punchthrough or punch adj2 through))	USPAT; US-PGPUB	2004/08/23 15:52
-	76	anneal\$4 and (ldd and (pocket with (punchthrough or punch adj2 through)))	USPAT; US-PGPUB	2004/08/23 16:27
-	3395	(pocket or halo) with implant\$5	USPAT; US-PGPUB	2004/08/23 16:28
-	697715	interconnect\$5 or wiring	USPAT; US-PGPUB	2004/08/23 16:29
-	11144	ldd	USPAT; US-PGPUB	2004/08/23 16:29
-	14669	ldd or light\$3 adj5 drain	USPAT; US-PGPUB	2004/08/23 16:29
-	206	((pocket or halo) with implant\$5) and (interconnect\$5 or wiring) and (ldd or light\$3 adj5 drain) and anneal\$4	USPAT; US-PGPUB	2004/08/23 16:30
-	1105431	hydrogen or "h2" or "h.sub.2" or "h.sub2."	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/25 10:05
-	1828622	plasma or discharg\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/25 10:04
-	23926	(hydrogen or "h2" or "h.sub.2" or "h.sub2.") near5 (plasma or discharg\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/25 10:06
-	1437627	damag\$4 or defect	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/25 10:06
-	1786934	etch\$4 or pattern\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/25 10:06
-	158349	polysi or polysilicon or (polycrystal\$4 or poly) adj2 (si or silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/25 10:07
-	1545	(damag\$4 or defect) with (etch\$4 or pattern\$4) with (polysi or polysilicon or (polycrystal\$4 or poly) adj2 (si or silicon))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/25 10:08
-	2	((hydrogen or "h2" or "h.sub.2" or "h.sub2.") near5 (plasma or discharg\$3)) same ((damag\$4 or defect) with (etch\$4 or pattern\$4) with (polysi or polysilicon or (polycrystal\$4 or poly) adj2 (si or silicon)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/25 10:10

-	53776	(damag\$4 or defect) with (etch\$4 or pattern\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/25 10:10
-	187	((hydrogen or "h2" or "h.sub.2" or "h.sub2.") near5 (plasma or discharg\$3)) same ((damag\$4 or defect) with (etch\$4 or pattern\$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/25 10:13
-	881572	gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/25 10:13
-	78	((hydrogen or "h2" or "h.sub.2" or "h.sub2.") near5 (plasma or discharg\$3)) same ((damag\$4 or defect) with (etch\$4 or pattern\$4))) and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/25 10:14
-	85621	(etch\$4 or pattern\$4) with gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/25 10:15
-	46	((hydrogen or "h2" or "h.sub.2" or "h.sub2.") near5 (plasma or discharg\$3)) same ((damag\$4 or defect) with (etch\$4 or pattern\$4))) and ((etch\$4 or pattern\$4) with gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/25 10:44
-	2	("5350710").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/25 10:44